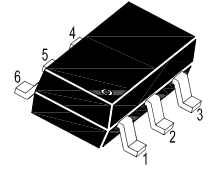
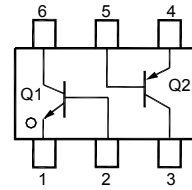


■ NPN / PNP Silicon Epitaxial Planar Transistors



1. Emitter 2. Base 3. Collector
4. Emitter 5. Base 6. Collector

■ Simplified outline(SOT-363)

■ Q1 Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	180	V
Collector Emitter Voltage	V_{CEO}	160	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	0.2	A
Power Dissipation	P_{tot}	0.2	W
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

■ Q2 Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	160	V
Collector Emitter Voltage	$-V_{CEO}$	150	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	0.2	A
Power Dissipation	P_{tot}	0.2	W
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

■ Q1 Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$ at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$ at $V_{CE} = 5\text{ V}$, $I_C = 50\text{ mA}$	h_{FE}	80 100 30	- 300 -	- - -
Collector Base Cutoff Current at $V_{CB} = 120\text{ V}$	I_{CBO}	-	0.05	μA
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$	I_{EBO}	-	0.05	μA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	180	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	160	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$ at $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$	$V_{CE(sat)}$	- -	0.15 0.2	V
Base Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$ at $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$	$V_{BE(sat)}$	- -	1 1	V
Current Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	100	300	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$	C_{ob}	-	6	pF

■ Q2 Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 1\text{ mA}$ at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$ at $-V_{CE} = 5\text{ V}$, $-I_C = 50\text{ mA}$	h_{FE}	50 100 50	- 300 -	- - -
Collector Base Cutoff Current at $-V_{CB} = 120\text{ V}$	$-I_{CBO}$	-	50	nA
Emitter Base Cutoff Current at $-V_{EB} = 3\text{ V}$	$-I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	160	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	150	-	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 1\text{ mA}$ at $-I_C = 50\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	- -	0.2 0.5	V
Base Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 1\text{ mA}$ at $-I_C = 50\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{BE(sat)}$	- -	1 1	V
Current Gain Bandwidth Product at $-V_{CE} = 10\text{ V}$, $-I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	100	300	MHz
Output Capacitance at $-V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$	C_{obo}	-	6	pF

Q1(NPN transistor)

Fig. 1 $h_{FE} - I_C$

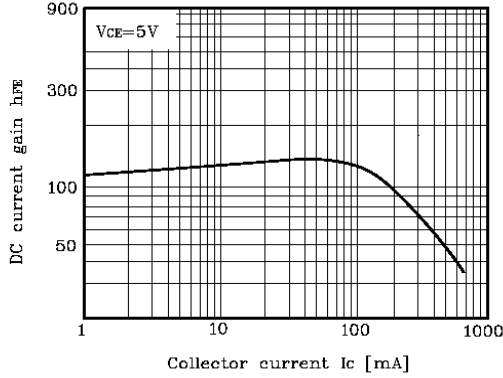


Fig. 2 $I_C - V_{BE}$

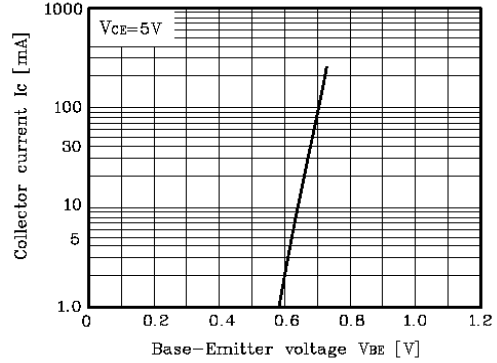


Fig. 3 $f_T - I_C$

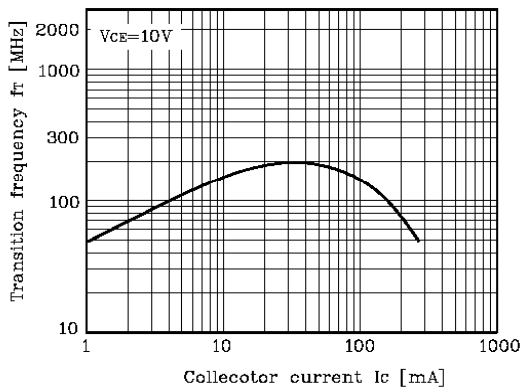


Fig. 4 $V_{CE(sat)}, V_{BE(sat)} - I_C$

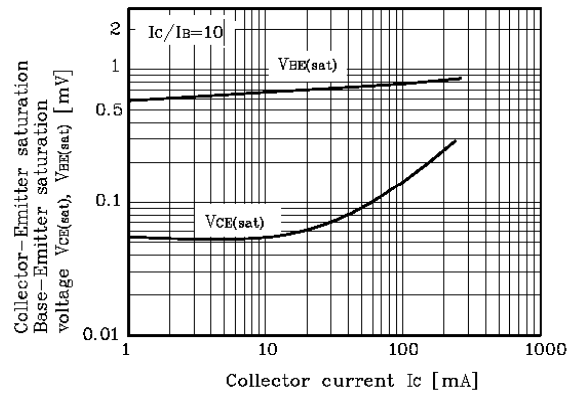


Fig. 5 $C_{ob} - V_{CB}$

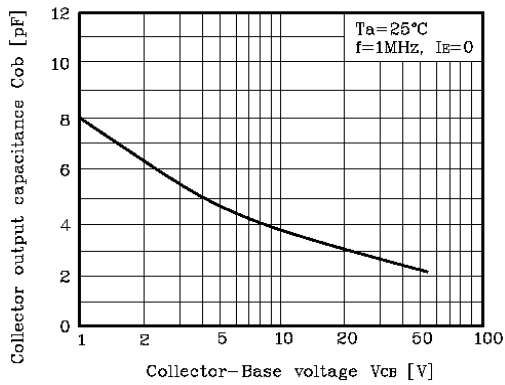
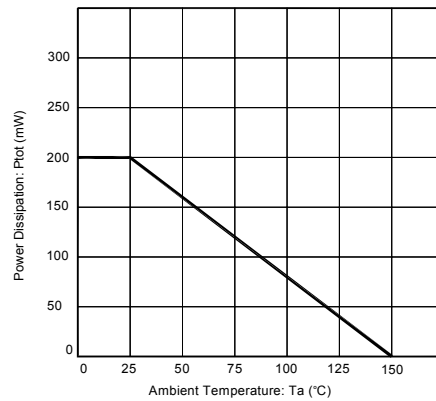


Fig. 6 $P_{tot} - T_a$



Q2(PNP transistor)

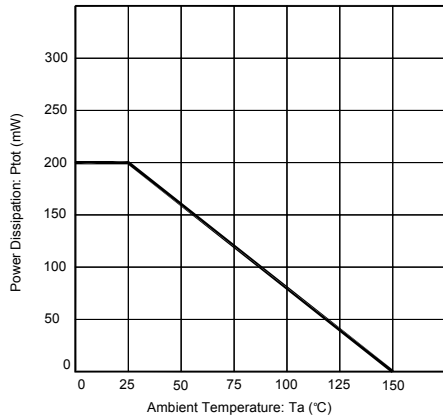


Fig.1 Max Power Dissipation vs Ambient Temperature

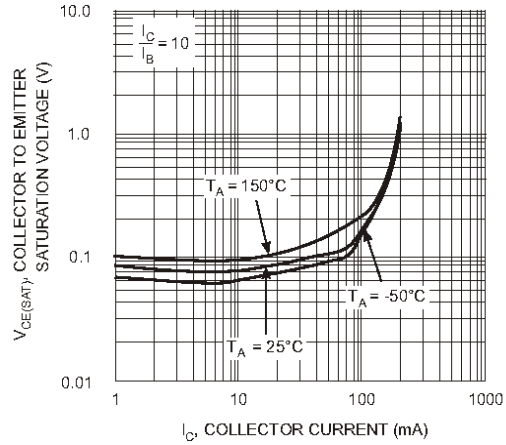


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

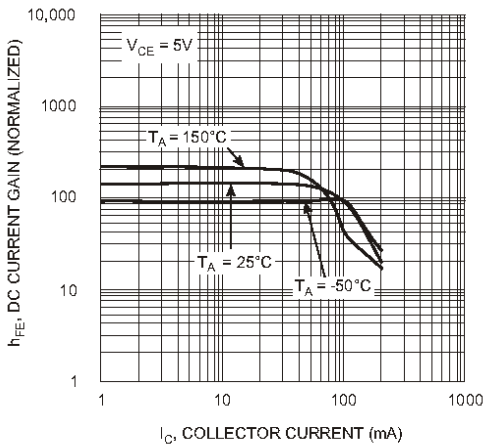


Fig. 3, DC Current Gain vs. Collector Current

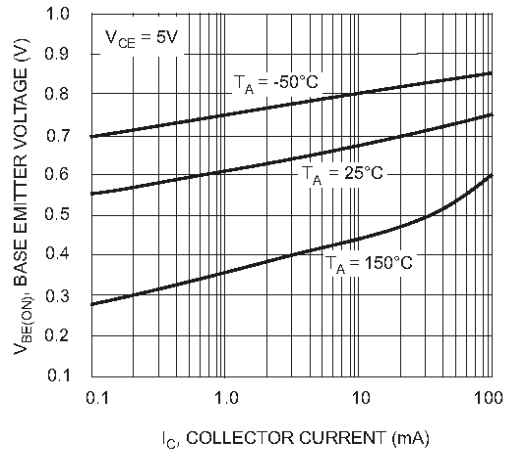


Fig. 4, Base Emitter Voltage vs. Collector Current

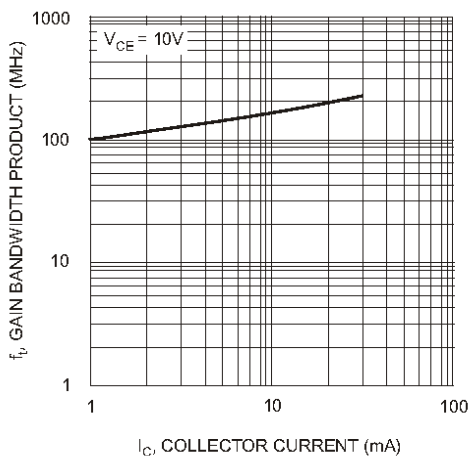
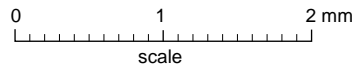
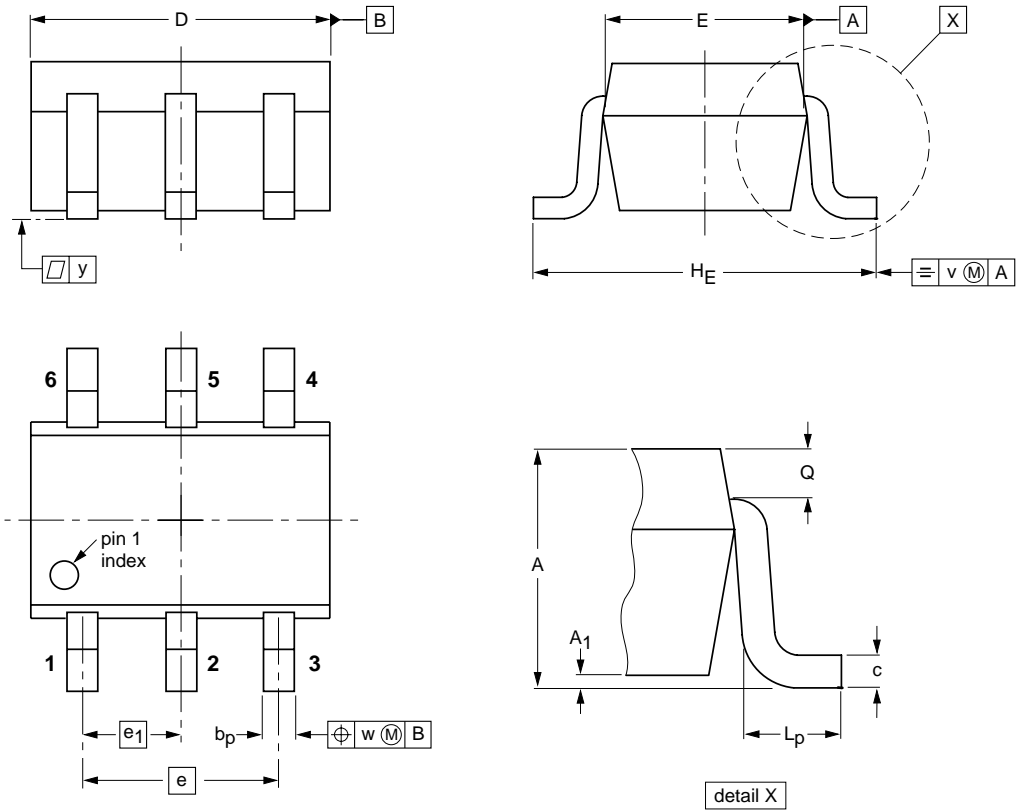


Fig. 5, Gain Bandwidth Product vs Collector Current

Package Outline

SOT-363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

Summary of Packing Options

Package	Package Description	Packing Quantity	Industry Standard
SOT-363	Tape/Reel, 7" reel	3000	EIA-481-1

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